

EAST Search History

EAST Search History (Prior Art)

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|---------------------|
| L1 | 93 | measur\$3 and polycrystalline adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:04 |
| L2 | 63 | photovoltaic adj devices and (slicing or dice\$3 or diced)and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:05 |
| L3 | 0 | defect adj characteriz\$3 and classificat\$3 and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:07 |
| L4 | 54 | defect and classificat\$3 and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:08 |
| L5 | 0 | (defects or grain adj boundaries)and processing adj wafer\$1 and classificat\$3 and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:09 |
| L6 | 75 | (defects or grain adj boundaries)and processing adj wafer\$1 and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:10 |
| L7 | 3 | L1 and L2 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:10 |
| L8 | 0 | L6 and L7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:11 |
| L9 | 0 | L7 and(defects or grain adj boundaries)and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:11 |

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|-----|----|--|---|----|----|---------------------|
| L10 | 0 | L7 and(defects or grain adj boundaries) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:12 |
| L11 | 0 | L7 and defects and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:12 |
| L12 | 10 | L2 and(imaging or ood or camera or CMOS or IR) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:15 |
| L13 | 3 | L12 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:16 |
| L14 | 0 | L2 and inspect\$3 adj defects and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:29 |
| L15 | 0 | L2 and inspect\$3 and defects and crystal adj growth and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:29 |
| L16 | 4 | L2 and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:30 |
| L17 | 1 | L16 and(defects or grain adj boundaries) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:30 |
| L18 | 0 | L17 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:30 |
| L19 | 55 | L2 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:35 |
| L20 | 1 | L19 and(imaging or ood or camera or CMOS or IR)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:35 |

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|-----|----|--|---|----|----|---------------------|
| L21 | 0 | L20 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:36 |
| L22 | 55 | L2 and L19 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:36 |
| L23 | 20 | L22 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:36 |
| L24 | 13 | L23 and(compar\$3 or match\$3) and(wafer or ingot or cells or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:44 |
| L25 | 11 | L23 and(compar\$3 or match\$3) same(wafer or ingot or cells or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:46 |
| L26 | 11 | L25 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:46 |
| L27 | 0 | L23 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:49 |
| L28 | 0 | L23 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:50 |
| L29 | 0 | L19 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:50 |
| L30 | 0 | L2 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:51 |
| L31 | 0 | L2 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:51 |

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|-----|----|---|---|----|----|---------------------|
| L32 | 0 | L1 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:52 |
| L33 | 0 | L6 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:52 |
| L34 | 0 | L2 and(imaging or ccd or camera or CMOS or IR)and (compar\$3 or match\$3)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:53 |
| L35 | 5 | (imaging or ccd or camera or CMOS or IR)and(compar\$3 or match\$3)and photovoltaic adj devices and(slicing or dice\$3 or diced)and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:54 |
| L36 | 2 | L35 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:54 |
| L37 | 2 | L36 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 10:55 |
| L38 | 4 | L2 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:04 |
| L39 | 10 | L1 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:04 |
| L40 | 0 | L38 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3)and surface adj wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:04 |
| L41 | 0 | L38 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:05 |
| L42 | 0 | L39 and(imaging or ccd or camera or CMOS or IR)and wafer adj image and cell adj image and(compar\$3 or match \$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:05 |

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|-----|---|---|---|----|----|---------------------|
| L43 | 0 | L39 and(imaging or ccd or camera or CMOS or IR)and (compar\$3 or match\$3)and photovoltaic adj devices and (slicing or dice\$3 or diced)and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:05 |
| L44 | 0 | L39 and(imaging or ccd or camera or CMOS or IR)and (compar\$3 or match\$3)and (cell adj solar or cell or memory or wafer\$1) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:06 |
| L45 | 4 | L39 and(imaging or ccd or camera or CMOS or IR) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:06 |
| L46 | 4 | L45 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:06 |
| L47 | 1 | L46 and(defects or variances or voids or defects or stacking adj faults or inclusions or impurities or grain or crystal adj boundaries) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:07 |
| L48 | 0 | L1 and produc\$4 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:16 |
| L49 | 0 | L2 and produc\$4 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:16 |
| L50 | 0 | L4 and produc\$4 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:16 |
| L51 | 0 | L4 and(produc\$4 or obtaining) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:16 |
| L52 | 0 | L39 and(produc\$4 or obtaining) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:17 |
| L53 | 0 | L35 and(produc\$4 or obtaining) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:17 |

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| L54 | 0 | L37 and (product\$4 or obtaining) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:17 |
| L55 | 1 | crystallographic adj structure and (product\$4 or obtaining) and wafer adj image and cell adj image and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:18 |
| L56 | 1 | crystallographic adj structure and (product\$4 or obtaining) and wafer adj image and (cell adj image or cells or cell or wafer or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:20 |
| L57 | 3130 | crystallographic adj structure and (product\$4 or obtaining) and (cell adj image or cells or cell or wafer or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:20 |
| L58 | 2 | L57 and photovoltaic adj devices and (slicing or dice\$3 or diced) and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:21 |
| L59 | 2 | L58 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/11 11:21 |
| S1 | 2124 | sheela chawan.Xa. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:40 |
| S2 | 2338 | sheela chawan.Xp. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:46 |
| S3 | 2 | S1 and wafer adj polishing | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:46 |
| S4 | 2 | S2 and wafer adj polishing | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:47 |
| S5 | 22 | S1 and wafer adj inspection | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:48 |

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| S6 | 22 | S2 and wafer adj inspection | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 15:48 |
| S7 | 156 | wafer adj pad and inspection | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/09 16:05 |
| S8 | 156 | wafer adj pad and inspection | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:04 |
| S9 | 27 | S8 and notch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:04 |
| S10 | 337122 | crystallographic asj structure and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:09 |
| S11 | 966 | crystallographic adj structure and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:09 |
| S12 | 191 | crystallographic adj structure same wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:09 |
| S13 | 150 | S12 and (@ad<"20040202" or @lad<"20040202" or @prad<"20040202" or @ptad<"20040202") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:21 |
| S14 | 117 | S12 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:21 |
| S15 | 16 | S14 and(solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:22 |
| S16 | 16 | S15 and (compar\$3 or match \$3)and wafer and(solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:23 |

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|-----|-----|---|---|----|-----|---------------------|
| S17 | 41 | crystallographic adj structure and wafer and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:39 |
| S18 | 5 | S17 and (compa\$3 or match\$3) and wafer and (solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:40 |
| S19 | 4 | S18 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:40 |
| S20 | 110 | ((("4352948") or ("6161054") or ("5203005") or ("5287472") or ("5292677") or ("5485097") or ("6243308") or ("4435498") or ("4471483") or ("4493055") or ("4519035") or ("4543444") or ("4898835") or ("4999689") or ("5019736") or ("5024972") or ("5252507") or ("5265847") or ("5315130") or ("5362666") or ("5393617") or ("5478363") or ("5491665") or ("5536964") or ("5552243") or ("5619419") or ("5624771") or ("5656392") or ("5657284") or ("5698453") or ("5698342") or ("5716459") or ("5808947") or ("5821160") or ("5851693") or ("5926419") or ("6040912") or ("RE36644") or ("6046078") or ("6140140") or ("6161213") or ("6225167") or ("6330819") or ("4304641") or ("4338480") or ("4353160") or ("4385198") or ("4400221") or ("4400868") or ("").pn.")). PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2010/03/10 16:43 |
| S21 | 106 | S20 and (@ad< "20040202" or @riad< "20040202" or @prad< "20040202" or @piad< "20040202") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:43 |
| S22 | 106 | S20 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:43 |
| S23 | 0 | S22 and crystallographic adj structure and wafer and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:44 |

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|-----|---------|--|---|----|----|---------------------|
| S24 | 0 | S22 and crystallographic adj structure and wafer and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 16:46 |
| S25 | 5 | S22 and inspect\$3 and (crystallographic adj structure or wafer or ingot or cells or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:05 |
| S26 | 4 | S25 and (compar\$3 or match\$3) and (solar adj cell or cell crystallographic adj structure or wafer or ingot or cells or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:06 |
| S27 | 4 | S26 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:07 |
| S28 | 4742 | crystallographic adj structure | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:10 |
| S29 | 4328355 | (wafer\$1 or semiconductor or solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:11 |
| S30 | 98638 | S29 and inspect\$3 and (cells or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:20 |
| S31 | 153527 | S29 and inspect\$3 and (cells or cell or wafer or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:21 |
| S32 | 4742 | crystallographic adj structure | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:22 |
| S33 | 632 | S31 and S32 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:27 |
| S34 | 1 | S33 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:28 |

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|-----|----|--|---|----|----|---------------------|
| S35 | 3 | inspect\$3 and solar adj cell and matrix and convert\$3 and electricity and solar adj cell and treating and silicon adj wafers and ingot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:32 |
| S36 | 2 | S35 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:33 |
| S37 | 1 | S35 and (compar\$3 or match \$3)and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:39 |
| S38 | 1 | S32 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:40 |
| S39 | 17 | S29 and (compar\$3 or match \$3)and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:40 |
| S40 | 3 | S39 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:41 |
| S41 | 1 | S39 and crystallographic adj structure | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:51 |
| S42 | 1 | S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell and crystallographic adj image and information and sufficient adj establish and correspondence and cell and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:58 |
| S43 | 1 | S39 and crystallographic adj structure and wafer adj structure and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:59 |
| S44 | 1 | crystallographic adj structure and wafer adj structure and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 17:59 |

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|-----|-----|--|---|----|----|---------------------|
| S45 | 2 | S29 and crystallographic adj structure and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:00 |
| S46 | 0 | S45 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:01 |
| S47 | 1 | S32 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:04 |
| S48 | 607 | S32 and inspect\$3 and(cells or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:06 |
| S49 | 1 | S48 and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:06 |
| S50 | 587 | S48 and(compar\$3 or match\$3) and (memory or cell or memory adj cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:07 |
| S51 | 1 | S48 and(compar\$3 or match\$3) same(memory or cell or memory adj cell)same wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:08 |
| S52 | 1 | S50 and crystallographic adj structure and wafer adj structure and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:09 |
| S53 | 1 | S50 and wafer adj structure and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:09 |
| S54 | 1 | S50 and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:10 |
| S55 | 297 | S50 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:10 |

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|-----|------|--|---|----|----|---------------------|
| S56 | 12 | S55 and(compar\$3 or match\$3) and wafer and(solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:11 |
| S57 | 13 | S55 and inspect\$3 and wafer \$1 and(cells or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:12 |
| S58 | 0 | S55 and inspect\$3 adj wafer\$1 same(cells or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:13 |
| S59 | 0 | S55 and inspect\$3 adj wafer\$1 and(cells or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:13 |
| S60 | 3559 | S28 and(wafer\$1 or semiconductor or solar adj cell or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:14 |
| S61 | 2 | S60 and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:14 |
| S62 | 0 | S61 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:14 |
| S63 | 2 | S32 and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:15 |
| S64 | 1818 | S32 and(wafer\$1 or semiconductor or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:16 |
| S65 | 237 | S32 and(wafer\$1 or semiconductor or memory)and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:16 |
| S66 | 119 | S65 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:16 |

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| S67 | 12 | S66 and (compar\$3 or match\$3) and wafer and (solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:19 |
| S68 | 38 | S32 and inspect\$3 and (compar\$3 or match\$3) and wafer and (solar adj cell or cell) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:28 |
| S69 | 41 | S32 and inspect\$3 and (compar\$3 or match\$3) and wafer and (solar adj cell or cell or memory) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:29 |
| S70 | 13 | S69 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:29 |
| S71 | 85837 | analyz\$3 and (crystalline or crystallographic adj structure) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:35 |
| S72 | 18 | S71 and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:36 |
| S73 | 1 | S72 and (wafer\$1 or semiconductor or memory) and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:36 |
| S74 | 1 | inspect\$3 and photovoltaic adj area and manufactured and crystalline adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:43 |
| S75 | 0 | S74 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:44 |
| S76 | 0 | S72 and (imaging or ccd or camera or CMOS or IR) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:46 |
| S77 | 0 | S71 and (imaging or ccd or camera or CMOS or IR) and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:47 |

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| S78 | 31037 | S71 and(imaging or cod or camera or CMOS or IR) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:47 |
| S79 | 8 | S78 and manufactured adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:47 |
| S80 | 2 | S79 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:48 |
| S81 | 2106 | S78 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:51 |
| S82 | 45 | S81 and(compar\$3 or match\$3) same(memory or cell or memory adj cell)same wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:52 |
| S83 | 18 | S82 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 18:52 |
| S84 | 25 | S17 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 19:17 |
| S85 | 5 | S72 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 19:48 |
| S86 | 118795 | (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 19:49 |
| S87 | 9 | S86 and(imaging or cod or camera or CMOS or IR)and wafer adj image and cell adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 19:49 |
| S88 | 1 | S87 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 19:49 |

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| S89 | 533 | crystallographic adj structure and(wafer or ingot)and section | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:15 |
| S90 | 161 | S89 and analyz\$3 and (crystalline or crystallographic adj structure) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:16 |
| S91 | 0 | S89 and analyz\$3 and (crystalline or crystallographic adj structure) same ignot | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:16 |
| S92 | 0 | S90 and(imaging or cod or camera or CMOS or IR)and wafer adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:17 |
| S93 | 120 | S90 and(imaging or cod or camera or CMOS or IR) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:17 |
| S94 | 48 | S93 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:22 |
| S95 | 0 | S93 and etching and texturisation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 20:59 |
| S96 | 7 | (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit) and etching and texturisation and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:00 |
| S97 | 2 | S96 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:00 |
| S98 | 0 | S97 and(compar\$3 or match\$3) same(memory or cell or memory adj cell or die)same wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:01 |
| S99 | 0 | S97 and(compar\$3 or match\$3) and(memory or cell or memory adj cell or die)and wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:01 |

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| S100 | 2 | S97 and(memory or cell or memory adj cell or die)and wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:01 |
| S101 | 161 | S89 and S90 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:05 |
| S102 | 0 | S101 and(wafer\$1 or semiconductor\$1 or IC or integrated adj circuit)and etching and texturisation and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:06 |
| S103 | 0 | S101 and etching and texturisation and inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:06 |
| S104 | 0 | S101 and etching and texturisation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:07 |
| S105 | 1 | S89 and etching and texturisation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:07 |
| S106 | 20 | S89 and solar adj cell | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:08 |
| S107 | 8 | S106 and @ad<"20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:08 |
| S108 | 2468 | ingot and production adj process | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:10 |
| S109 | 523 | S108 and wafer\$3 and production adj process | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:11 |
| S110 | 128 | S109 and cell and production adj process | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:11 |

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| S111 | 1 | S110 and wafer adj position\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:12 |
| S112 | 75 | S110 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:13 |
| S113 | 0 | S112 and cell adj inspect\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:13 |
| S114 | 75 | S112 and(memory or cell or memory adj cell or die)and wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:14 |
| S115 | 0 | S114 and(imaging or ccd or camera or CMOS or IR)and wafer adj image | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:14 |
| S116 | 12 | S114 and(imaging or ccd or camera or CMOS or IR) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:14 |
| S117 | 10 | S116 and(compar\$3 or match \$3)and(memory or cell or memory adj cell or die)and wafer\$1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:15 |
| S118 | 10 | S117 and @ad< "20040202" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/03/10 21:15 |

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